	CT					File No.:	YC124-02
	SYI	NTOP	N-TECH CO	JKF	PORATION	Version:	В
			CHIP NET	NOF	RK	Page: Date:	1/22 2012.11.23
							2012.11.23
I.SUBJ	ECT :	This spe	cification applies	s on th	e chip resistors ne	etwork	
		was ma	de by SYNTON	-TEC	H Corporation _o		
2.PART	NUM	BER : P	art number of the	e chip	resistor is identifi	ed	
		b	y the No. of Res	istors,	tolerance, resistar	nce value	o
-			ΠΙΠΤΙΛΝ	N 76		5 0/ 1/	017
Exam	ple :	DESC	<u>RIPTION :</u>	<u>Y(</u>	C12 8P4R	<u>5% 1</u>	<u>0K</u>
		<u>SYN</u>	FON CODE	<u>: \</u>	<u>C12 4R</u>	<u> </u>	03
	I						
	↓ ↓		•				Ĺ.
<u>Pr</u>	oduct	_	<u>Style</u>		<u>Tolerance</u>	Res	<u>sistance</u>
	CHIP		8Pin / 4R		F:±1%		7-1 -
NET	WORK		for		J:±5%		Value
			0402 x 4			E24	Series 5%
			Elements			3	Digits :
						2R	2:2.2Ω
						10	ι:100Ω
						10.	3:10K
						10	5 : 1M
						EQ	Series 1%
							Digits :
			(Please see				20:2.2Ω
			detail of			10	00 : 100Ω
			Figure1)			10	02 : 10K
						10	04 : 1M
APPROVED	Сче		DESIGNED		REMARK		MENT NO.
Carol		lay	Chen	RE:S	SGS	02010)10093
L						Confidentu	al, Do Not Disseminate.

SYNTON-TECH CORPORATION File No.: Version: Version: CHIPNETWORK Page: Date: Date:

 on:
 B

 e:
 2/22

 e:
 2012.11.23

YC124-02

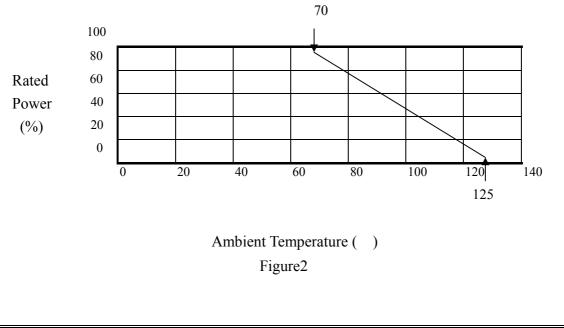
3.ELECTRICAL CHARACTERISTICS

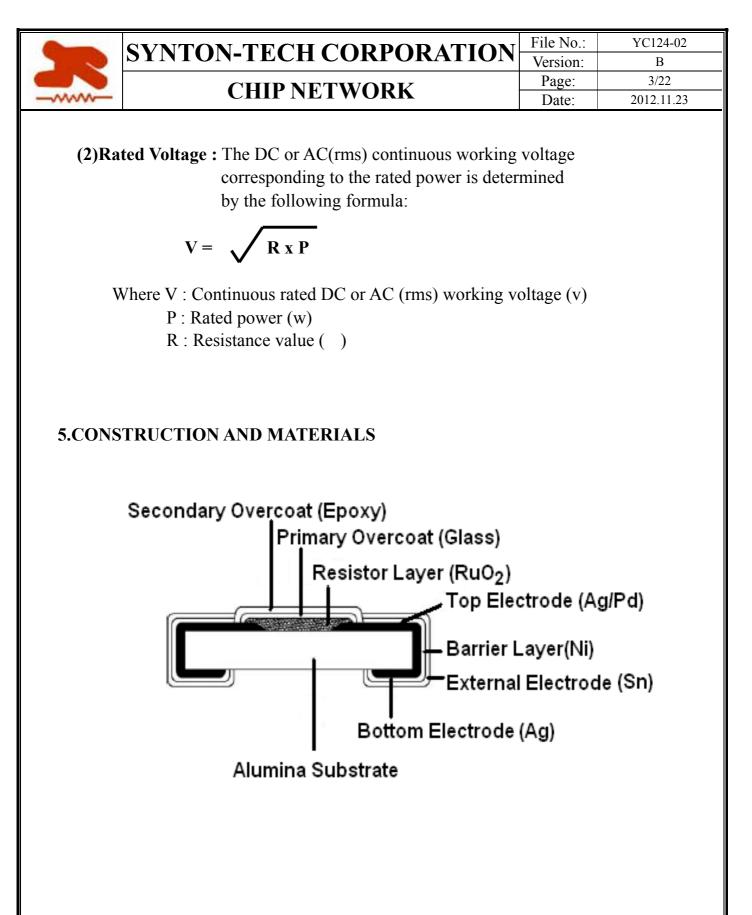
STYLE	YC124
POWER	1/16W (0402)
Maximum Working Voltage	50V
Maximum Overload Voltage	100V
Dielectric Withstand Voltage	100V
No. of resistors	8P4R
Resistance Range	$10\Omega \sim 1M\Omega$
Operating Temp. Range	-55 ~+125
Temperature Coefficient (± PPM /)	±200PPM/

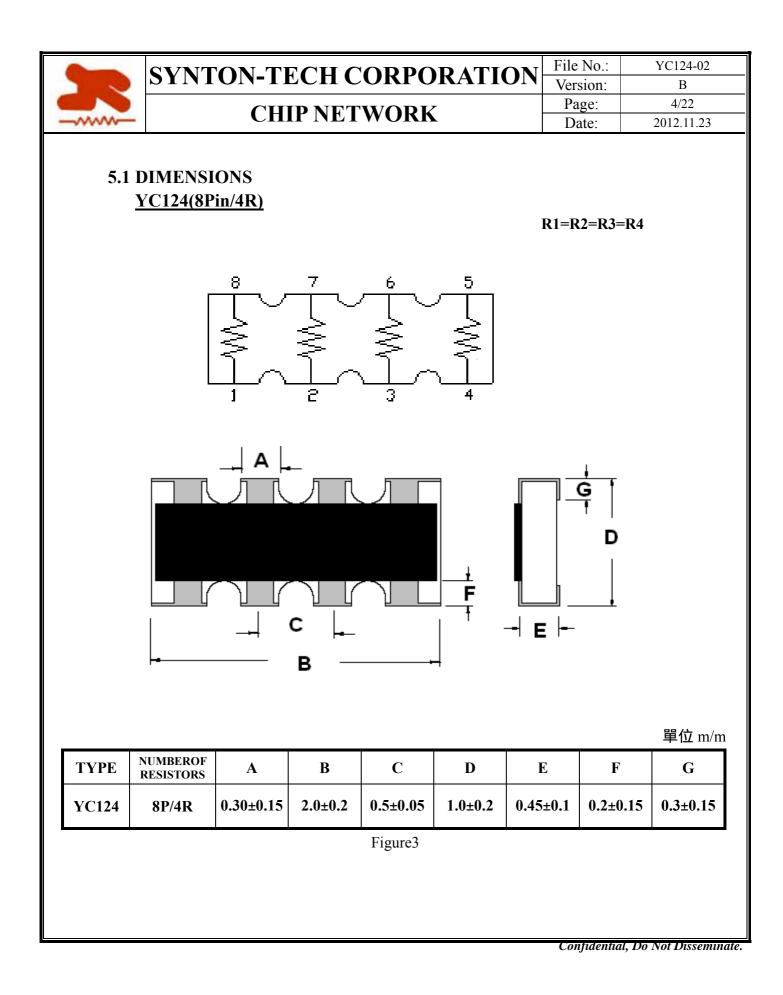
Figure 1

4. POWER RATING

(1)Power Derating : The rated power at the temperature in excess of 70 shall be derated in accordance with figure3







SYNTON-TECH CORPORATION	File No.:	YC124-02
SINION-IECH CORFORATION	Version:	В
CHIDNETWODK	Page:	5/22
 CHIP NETWORK	Date:	2012.11.23

6. CHARACTERISTICS

(1) Temperature Coefficient of Resistance(T.C.R.)

Test Method : Measure resistance at +25 or specified room temperature as R1, then measure at -55 and +125 respectively as R2. Determine the temperature coefficient of Resistance from the following formula.

R2 - R1

T. C. R. = $\underline{\qquad}$ X 10⁶ (p p m /) R1 (t2 - t1) Where t1 = +25 or specified room temperature t2 = -55 or +125 ±3

(2) Thermal Shock

Test Method : -55 for 2 minutes and +125 for 2 minutes as One cycle, after 5 cycles the specimen shall be Stabilized at room temperature for one hour Minimum and then measure the R/R(%).

Acceptance Standard : $\pm (1.0\% + 0.05)$

(3) Low Temperature Operation

Test Method :Place the specimen in a test chamber maintained at -55 . After one hour stabilization at this temperature, full rated working voltage shall be applied for 45 minutes. 15 minutes after remove the voltage, the specimen shall be removed from the chamber and stabilized at room temperature for 24 hours minimum. Measure R/R(%).

Acceptance Standard : $\pm (1.0\% + 0.05)$ No mechanical damage.



SYNTON-TECH CORPORATIONFile No.:
Version:CHIP NETWORKPage:
Date:

YC124-02

(4) Short Time Overload

Test Method : Apply 2.5 times of rated voltage but not exceeding the maximum overload voltage 1 for 5 seconds. Have the specimen stabilized at room temperature for 30 minutes minimum. Measure the R/R(%).

Acceptance Standard : $\pm (2.0\% + 0.05)$) No evidence of mechanical damage.

(5) High Temperature Exposure

Test Method : Place the specimen in an oven at 125 ± 5 for 100 hours. Remove the specimen from the oven and stabilize at room temperature for one hour minimum. Measure the R/R(%).

Acceptance Standard : $\pm (2.0\% + 0.1)$

(6) Resistance to Soldering Heat

Test Method : Immerse the specimen in the solder pot at 260±5 for 10±1 seconds. Have the specimen stabilized at room temperature for 30 minutes minimum. Measure the R/R(%).

Acceptance Standard : $\pm(1.0\%+0.05)$)

(7) Moisture Resistance

Test Method : Place the specimen in a test chamber at 40 ± 2 and 90~95% relative humidity. Apply the rated voltage to the specimen at the 1.5 hours on and 0.5 hour off cycle. The total length of test is 1000 +48/-0 Hrs. After the test, have the specimen stabilized at room temperature for one hour minimum. Measure the R/R(%).

Acceptance Standard : $\pm (3.0\% + 0.1)$



SYNTON-TECH CORPORATION File No.: Version: CHUR NETWORK Page:

CHIP NETWORK

YC124-02

(8) Load Life

Test Method : Place the specimen in the over at 70 ± 2 . Apply the rated voltage to the specimen at 1.5 hours on and 0.5 hour off cycle. The total length of test is 1000 +48/-0 hours. After the test have the specimen stabilized at room temperature for one hour minimum and measure the R/R(%).

Acceptance Standard : $\pm(3.0\%+0.1)$

(9) Solderability

Test Method : Immerse the specimen in the solder pot at 245±5 for 5 seconds

Acceptance Standard : At least 95% solder coverage on the termination

(10) Bending Strength

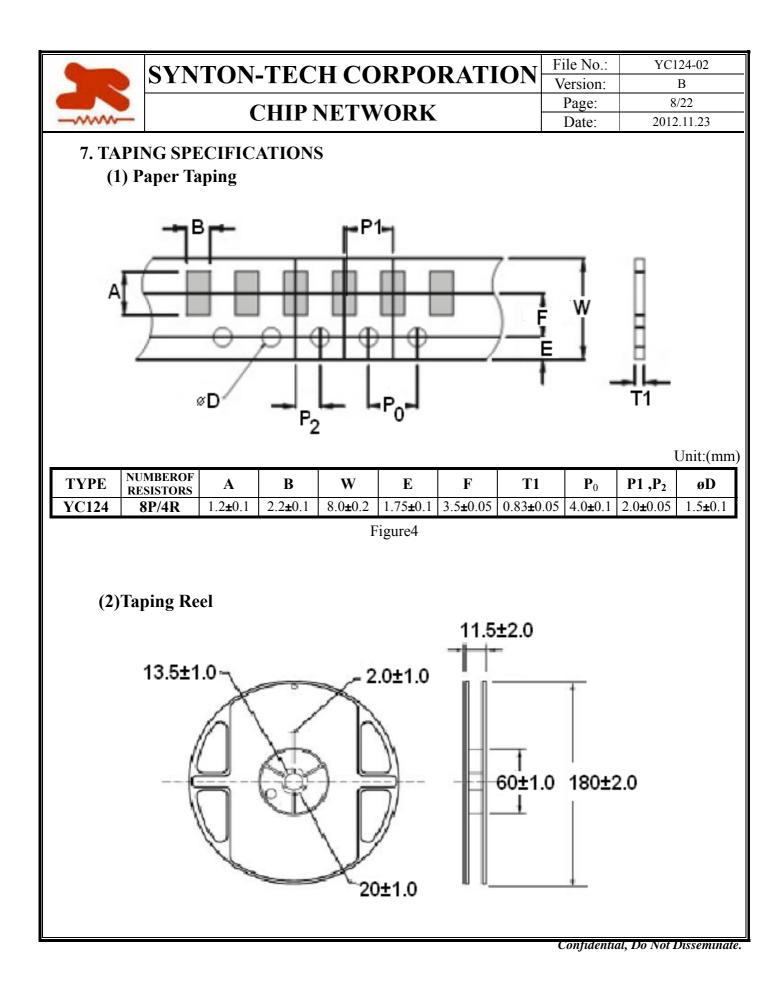
Test Method : Mount the specimen on a test board . Slowly apply the force till the board is bend at 5+0.2mm for 5 ± 1 seconds, and measure the R/R(%)at this position.

Acceptance Standard : $\pm (1.0\% + 0.05)$)

(11) Insulation Resistance

Test Method : Place the specimen in the jig and apply a 500Vdc voltage for one minute. Measure the insulation resistance.

Acceptance Standard : 1,000M minimum.



SVNTON TECH CODDOD ATION	File No.:	YC124-02
SYNTON-TECH CORPORATION	Version:	В
CHIP NETWORK	Page:	9/22
	Date:	2012.11.23

	SYNTON-TECH CORPOR		File No.:	YC124-02	
	SINION-IECH CORPOR	AIIUN	version.	В	
	CHIP NETWORK		Page:	10/22	
~~~~~			Date:	2012.11.23	
	SGS 試報告				
KK AK SYNT	数码(No.) 1 KA/2012/30142A-07 日初 該均有限公司 ON-TECH CORPORATION		/31 頁載(Page)	t 1 of 13	
16F- TAII GUAN	市汐止區新台五路一段79號16樓之3/廣東省東莞市大胡鎮水口管理 3, NO.79, FAR EAST WORLD CENTER SEC.1, HS1N TAI WU ROAD, F E1 CITY ,TAIWAN, R.O.C./(DONG GUAN PLANL)SHU1 KOU INDUSTRI , GUANG DONG,CH1NA	ISI-CHIH DISTRICT, AL ZONE DA LANG,	DONG	7. V. D	
	测试揉品係由客户送揉,且由客户聲稿差經客户確認如下(The atified by/on behalf of the client as);	tollowing sample	s was/were sub	nitted and	
<b>根品</b> 收件	名稿(Sample Description) : LEAD FREE THICK FI 型號(Style/Item No.) : LEAD FREE THICK FI 日期(Sample Receiving Date) : 2012/03/02 期間(Testing Period) : 2012/03/02 TO 2012	LM CHIP RESISTORS			
30) ±1	.结果(Test Results) : 猜见下一页 (Please	refer to next pa	gee).		
SI	Ray Changes SGS y Chang / Asst. Manager pred for and on behalf of S Taiwan Limited				
This docu	services stated the results shown in this test report refer only to the sample(s) tosted. This tor any. PP2 月 年後月 - 定前こ前用道分前法之生体所見完 - 本和月 非法主公 可提供用用 - 不可定分別数 - nent is issued by the Company subject to its General Conditions of Service prioted overleaf, and tornat documents, subject to Term and Conditions for Decording Documents at view sgc.com provide and within the limits of Client's instructions, if any. The Company's sole reponability is all their rights and obligations under the transaction document, This document cannot be reprod forgery of falsification of the content or appearance of this document is unliavial and offenders ming <u>CG5 Telweet Ld</u> , 合常 性能性 14 (b) fals (c) and (c)	lable on request or accessite and remains and Conditions/Terral information contained here to its Client and this docum used except in hall, without pr / be prosecuted to the fullest / kephalung, Taiwan / 考:华中	le al www.sgs.con/lerm ms-e-Document. Attentio con reflects the Compan- sent does not exonesale sor written approval of the extent of the law.	Land, conditions.htm and, for nis drawn to the limitation of y's findings at the time of its parties to a barbaction from company. Any unauthorized TWA 7 5 6 9 1 4 0	1000

~~~~			CORPORATION	File No.:	
	1			Version:	
	СНП) NF1	ſWORK	Page:	11/22
				Date:	2012.11
測試	GS 報告 Report ^{就妈(No.)} :	KA/2012/3	0142A-07 日期(Date): 2012/10/31	頁數(Page) :	2 of 13
肤純酸份有 SYNTON-TEX 新北市汐止 16F-3, NO, TAIPE1 CIT GUAN, GUAS 囲気結果(作用公司 CH CORPORATION た医新台五路一段79號16樓之3/廣: .79, FAR EAST WORLD CENTER SEC TY ,TAIWAN, R.O.C./(DONG GUAN NG DONG,CHINA Test Results)	2.1. HSIN PLANL)SHU	大刻榮水口管理道 TAI WU ROAD, HSI-CHIH DISTRICT, NEW I KOU INDUSTRIAL ZONE DA LANG, DONG L LEAD FREE THICK FILM CHIP RESISTOR	S & CHIP AR	RAYS
			LACK/WHITE LEAD FREE THICK FILM CHIP	RESISTORS &	& CHIP ARRAYS)
	湖武項日 (Test Items)	單位 (Unit)	测试方法 (Method)	方法值测	結果 (Result) NO.1
绪 / Cadmi	ium (Cd)	ng/kg	参考IEC 62321: 2008方法。用感應稿合 電漿原子發射光谱儀檢測。/ With reference to IEC 62321: 2008 and performed by ICP-AES。	2	n.d.
3G / Lead	(Pb)	mg/kg	参考IEC 62321: 2008方法。用愚趣稿合 電漿原子發射光譜儀檢測。/ With reference to IEC 62321: 2008 and performed by ICP-AES,	2	209
承 / Mercu	ury (Hg)	mg/kg	参考1EC 62321: 2008方法,用感應稿合 電頻原子發射光谱儀檢測。/ With reference to 1EC 62321: 2008 and performed by ICP-AES.	2	n.d.
六價格 / 1	ury (Hg) Hexavalent Chromium Cr(V1) by extraction	mg/kg	電漿原子發射光譜儀檢測。/ With reference to IEC 62321: 2008 and		n.d.
六債络 /) alkaline e	Hexavalent Chromium Cr(VI) by		電頻原子發射光譜儀檢測。/ With reference to IEC 62321: 2008 and performed by ICP-AES. 參考IEC 62321: 2008方法, 用UV-VIS檢 詞。/ With reference to IEC 62321:	2	
云價格 / 1 alkaline。 多溴硼苯胡 一溴硼苯	Hexavalent Chromium Cr(VI) by extraction 急和 / Sum of PBBs / Monobromobiphenyl		電頻原子發射光譜儀檢測。/ With reference to IEC 62321: 2008 and performed by ICP-AES. 參考IEC 62321: 2008方法, 用UV-VIS檢 詞。/ With reference to IEC 62321:	2	n.d. n.d. n.d.
六價格 / J alkaline 多 決勝茶想 一 浅聯茶 二 洗聯茶	Hoxavalent Chromium Cr(VI) by extraction 急和 / Sum of PBBs / Monobromobiphenyl / Dibromobiphenyl		電頻原子發射光譜儀檢測。/ With reference to IEC 62321: 2008 and performed by ICP-AES. 參考IEC 62321: 2008方法, 用UV-VIS檢 詞。/ With reference to IEC 62321:	2	n.d. n.d. n.d. n.d.
六債格 / 1 alkaline 多 決聯茶却 二決聯茶 / 二 二決聯茶 / 三 決聯茶 /	Hexavalent Chromium Cr(VI) by extraction 包和 / Sum of PBBs / Monobromobiphenyl / Dibromobiphenyl / Tribromobiphenyl		電頻原于發射光譜儀檢測。/ With reference to IEC 62321: 2008 and performed by ICP-AES. 多考IEC 62321: 2008方法, 用UV-VIS撬 制。/ With reference to IEC 62321: 2008 and performed by UV-VIS. 參考IEC 62321: 2008方法, 以乳相層析	2 - 5 - 5 - 5 - 5 - 5 - 5 - 5 - 5 - 5 -	n.d. n.d. n.d.
六債務 / 1 () ())) ()))))))))))))	Hoxavalent Chromium Cr(VI) by extraction 急和 / Sum of PBBs / Monobromobiphenyl / Dibromobiphenyl		電頻原子發射光譜儀檢測。/ With reference to IEC 62321: 2008 and performed by ICP-AES. 多考IEC 62321: 2008方法, 用UV-VIS檢 例。/ With reference to IEC 62321: 2008 and performed by UV-VIS. 參考IEC 62321: 2008方法,以乳机層析 儀/質譜儀檢測。/ With reference to	2 5 5 5 5	n.d. n.d. n.d. n.d. n.d.
六債務 / 1 (債務 / 1 多 決聯基本 二 二 決聯基本 三 四 洗 聯基 本 4 5 2 2 3 3 3 3 3 3 3 3 3 3 3 3 3	Hexavalent Chromium Cr(VI) by extraction 名和 / Sum of PBBs / Monobromobiphenyl / Dibromobiphenyl / Tribromobiphenyl / Tetrabromobiphenyl	mg/kg	電頻原子發射光譜儀檢測。/ With reference to IEC 62321: 2008 and performed by ICP-AES. 參考IEC 62321: 2008方法。用UV-VIS檢 制。/ With reference to IEC 62321: 2008 and performed by UV-VIS. 參考IEC 62321: 2008方法。以我相層新 儀/質譜儀檢測。/ With reference to IEC 62321: 2008 and performed by	2 5 5 5 5 5 5	n.d. n.d. n.d. n.d. n.d. n.d.
 六債络 / 1 多 決場聯苯 ノニ三四五六決勝苯 ノニシ決勝苯 ノニシ決勝苯 ノン決勝苯 ノン決勝苯 	Hexavalent Chromium Cr(VI) by extraction 2 / Sum of PBBs / Monobromobiphenyl / Dibromobiphenyl / Tribromobiphenyl / Tetrabromobiphenyl / Pentabromobiphenyl / Hexabromobiphenyl / Heptabromobiphenyl	mg/kg	電頻原子發射光譜儀檢測。/ With reference to IEC 62321: 2008 and performed by ICP-AES. 多考IEC 62321: 2008方法, 用UV-VIS檢 例。/ With reference to IEC 62321: 2008 and performed by UV-VIS. 參考IEC 62321: 2008方法,以乳机層析 儀/質譜儀檢測。/ With reference to	2 5 5 5 5 5 5 5 5 5 5 5	n.d. n.d. n.d. n.d. n.d. n.d. n.d. n.d.
 六債络 / i 多一次線聯末 / シーニ三四五六七次際聯末 / ハ次聯苯 / ハ次聯苯 / 	Hexavalent Chromium Cr(VI) by extraction ** / Sum of PBBs / Monobromobiphenyl / Dibromobiphenyl / Tribromobiphenyl / Tetrabromobiphenyl / Pentabromobiphenyl / Hexabromobiphenyl	mg/kg	電頻原子發射光譜儀檢測。/ With reference to IEC 62321: 2008 and performed by ICP-AES. 參考IEC 62321: 2008方法。用UV-VIS檢 制。/ With reference to IEC 62321: 2008 and performed by UV-VIS. 參考IEC 62321: 2008方法。以我相層新 儀/質譜儀檢測。/ With reference to IEC 62321: 2008 and performed by	2 5 5 5 5 5 5 5 5 5	n.d. n.d. n.d. n.d. n.d. n.d. n.d. n.d.



SYNTON-TECH CORPORATION

CHIP NETWORK

File No.: YC124-02 Version: В Page: 12/22

Date: 2012.11.23



測試報告 **Test Report**

號碼(No.): KA/2012/30142A-07 日期(Date): 2012/10/31 頁數(Page): 3 of 13

欣挑股份有限公司

SYNTON-TECH CORPORATION

新北市沙止區新台五路一段79號16樓之3/廣東省東莞市大明鎮水口管理區 16F-3, NO.79, FAR EAST WORLD CENTER SEC.1, HSIN TAI WU ROAD, HSI-CHIH DISTRICT, NEW TAIPEI CITY , TAIWAN, R.O.C. / (DONG GUAN PLANL)SHUI KOU INDUSTRIAL ZONE DA LANG, DONG GUAN, GUANG DONG, CHINA

间就項目	單位	测试方法	方法值测 極限值	结果 (Result)
(Test Items)	(Unit)	(Method)	(MDL)	NO.1
多溴聯苯醚總和 / Sum of PBDEs			-	n.d.
一溴聯苯醚 / Monobromodiphenyl ether			5	n.d.
二溴聯苯醚 / Dibromodiphenyl ether			5	n.d.
三溴聯苯醚 / Tribromodiphenyl ether		A trung const. another with the Mate	5	n.d.
四溴聯苯醚 / Tetrabromodiphenyl ether		冬考1EC 62321: 2008方法,以氣相層析	5	n.d.
五溴聯苯醚 / Pentabromodiphenyl ether	ng/kg	儀/質譜儀檢測。/ With reference to IEC 62321: 2008 and performed by	5	n.d.
六溴聯苯醚 / Hexabromodiphenyl ether		GC/MS.	5	n.d.
七溴聯苯醚 / Heptabromodiphenyl ether		GC/85.	5	n.d.
へ溴聯苯醚 / Octabromodiphenyl ether			5	n.d.
九溴聯苯醌 / Nonabromodiphonyl other			5	n.d.
十溴醇苯醚 / Decabromodiphenyl ether			5	n.d.
南禾 / Halogen				
南柰 (泉) / Halogen-Fluorine (F) (CAS No.: 14762-94-8)	ng/kg	參考BS EN 14582:2007、以離子層析儀 分析、/ With reference to BS EN 14582:2007. Analysis was performed by IC.	50	n.d.
南素 (亂) / Halogen-Chlorine (Cl) (CAS No.: 22537-15-1)	ng/kg	冬考BS EN 14582:2007, 以離子層析儀 分析。/ With reference to BS EN 14582:2007. Analysis was performed by IC.	50	n.d.
由素 (決) / Halogen-Bromine (Br) (CAS No.: 10097-32-2)	ng/kg	冬考BS EN 14582:2007, 以離子層析儀 分析。/ With reference to BS EN 14582:2007, Analysis was performed by IC.	50	n.d.
由素 (映) / Halogen-lodine (I) (CAS No.: 14362-44-8)	ng/kg	冬考BS EN 14582:2007、以敵子層析儀 分析、/ With reference to BS EN 14582:2007、Analysis was performed by IC、	50	n.d.
三氧化二邻 / Antimony trioxide (Sb2O3)*** (CAS No.: 1309-64-4)	ng/kg	参考US EPA 3052方法,用島應稿合電漿 原子發射光譜儀檢詞梯含量。/ With reference to US EPA Method 3052 for Antimony Content. Analysis was performed by ICP-AES.		π.d.

S65 Teiwen Ltd. を溶液指針は設份有限公司 1(886-7)301-2121 1(886-7)301-0867 www.sgs.tw

Confidential, Do Not Disseminate.

Member at DGS Group



SYNTON-TECH CORPORATION

CHIP NETWORK

File No.: YC124-02 Version: В Page: 13/22

2012.11.23 Date:



测試報告 **Test Report**

號碼(No.): KA/2012/30142A-07 日期(Date): 2012/10/31 頁數(Page): 4 of 13

欣统股份有限公司

SYNTON-TECH CORPORATION

新北市沙止區新台五路一段79號16樓之3/廣東省東莞市大朗鎮水口管理區

16F-3, NO.79, FAR EAST WORLD CENTER SEC.1, HSIN TAI WU ROAD, HS1-CHIH DISTRICT, NEW TAIPEI CITY , TAIWAN, R.O.C./(DONG GUAN PLANL)SHUI KOU INDUSTRIAL ZONE DA LANG, DONG GUAN, GUANG DONG, CHINA

湖北項目 (Test Items)	單位 (Unit)	测試方法 (Method)	方法值测 極限值 (MDL)	结果 (Result) NO.1
全象寺犹靖馥 / Perfluorooctane sulfonates (PFOS - Acid, Metal Salt, Amide)	mg∕kg	參考US EPA 3540C: 1996方法,以淀相 層析質譜儀檢測全氣辛烷磺酸含量。/ With reference to US EPA 3540C: 1996 method for PFOS Content. Analysis was performed by LC/MS.	10	n.d.
全氣辛酸(鉄) / PFOA (CAS No.: 335-67- 1)	mg∕kg	孝考US EPA 3540C; 1996方法,以流相 層析質譜儀检測全氣辛酸(候)含量。/ With reference to US EPA 3540C; 1996 method for PFOA Content. Analysis was performed by LC/MS.	10	n.d.
绨 / Antimony (Sb)	mg/kg	参考US EPA 3052方法,用感應稱合電漿 原子發射光譜儀檢測歸含量。/ With reference to US EPA Method 3052 for Antimony Content. Analysis was performed by ICP-AES.	2	n.d.
紅嘴 / Red phosphorus		本詞試以熱裂解儀分析、/ Analysis was performed by Pyrolyzer-GC/MS.		Negative
可塑劑定量分析 / Plathalates				
鄰苯二甲酸甲苯基丁酯 / BBP (Benzyl butyl phthalate) (CAS No.: 85-68-7)	56	本測試參考EN 14372,以氣相層析儀/質 譜儀檢測之。/ With reference to EN 14372, Analysis was performed by GC/NS.	0.003	n.d.
鄭苯二甲酸二丁酯 / DBP(Dibuty) phthalate)(CAS No.: 84-74-2)	96	本測試參考EN 14372,以氣相層析儀/質 譜儀檢測之、/ With reference to EN 14372. Analysis was performed by GC/MS.	0.003	n.d.

505 Taiwan Ltd. 台湾依映科社取份有法会司 14886-7) 301-2121 1(886-7) 201-0867 www.sgs.tw

Mumber at BBS Group

Confidential, Do Not Disseminate.

2001





測試報告 Test Report

乾碼(No.): KA/2012/30142A-07 日期(Date): 2012/10/31 頁數(Page): 5 of 13

欣姚殷傍有限公司

SYNTON-TECH CORPORATION

新北市沙止區新台五路一段79號16樓之3/廣東省東莞市大胡鎮水口管理區

16F-3, NO.79, FAR EAST WORLD CENTER SEC.1, HSIN TAI WU ROAD, HSI-CHIH DISTRICT, NEW TAIPEI CITY ,TAIWAN, R.O.C./(DONG GUAN PLANL)SHUI KOU INDUSTRIAL ZONE DA LANG, DONG GUAN, GUANG DONG,CHINA

19] 3년 2월 년 (Test Items)	單位 (Unit)	测試方法 (Method)	方法值测 種限值 (MDL)	結果 (Result) NO.1
鄭苯二甲酸二 (2-乙基己基)商 / DEHP (Di- (2-ethylhexyl) phthalate) (CAS No.: 117-81-7)	55	本測試參考EN 14372.以氣相層析儀/質 譜儀檢測之, / With reference to EN 14372. Analysis was performed by GC/MS.	0.003	n.d.
都苯二甲酸二異癸酯 / DIDP (Di-isodecyl phthalate) (CAS No.: 26761-40-0)	55	本測試參考EN 14372,以氣相層析儀/質 譜儀檢測之,/With reference to EN 14372, Analysis was performed by GC/MS.	0.01	n.d.
郁芊二甲酸二異壬酯 / DINP(Di-isononyl phthalate)(CAS No.: 28553-12-0)	14	本測試參考EN 14372,以氣相層析儀/質 譜儀檢測之. / With reference to EN 14372, Analysis was performed by GC/MS.	0.01	n.d.
鄰苯二甲酸二正辛酯 / DNOP (Di-m-octyl phthalate) (CAS No.: 117-84-0)	%	本測試參考EN 14372,以氣相層析儀/質 譜儀檢測之. / With reference to EN 14372, Analysis was performed by GC/NS,	0.003	n.d.

Unless otherwise stated the results shown in this test report refer only to the sample(s) tested. This test report cannot be reproduced, except in full, without prior written permission of the Company. DEPT REVI + EXTERNITES ALL STATES ALL ST

Confidential, Do Not Disseminate.

200

Syntach Experimentation Version: B Page: 15/22 Date: 2012.11.23	SYNTON-TECH CORPORATION Version: B Page: 15/22 Date: 2012.11.23	Syntacon-frecch CockPorcation Version: B Page: 15/22 Date: 2012.11.23				
Version D Page: 15/22 Date: 2012.11.23 Date: 2012.11.23	Valuation D Page: 15/22 Date: 2012.11.23 Antipage: 15/22 Date: 2012.11.23 Antipage: 15/22 Date: 2012.11.23	<image/>		SYNTON-TECH CORPORATION	File No.:	
Yes Date: 2012.11.23 Yes Date: 2012.11.23 Secs Secs And Ref Secs Secs	Number Numer Numer Numer <td>CHIPMENTWORK Date: 201.11.23 Date</td> <td>~</td> <th></th> <td></td> <td></td>	CHIPMENTWORK Date: 201.11.23 Date	~			
 Agagaga Agagagaga Agagagaga Agagagagagaga Agagagagagagagagagagagagagagagagagagaga	 SGGSS Mgagag Betworth and the second s	<section-header></section-header>		CHIP NETWORK		
 	 By By B	<section-header><section-header><section-header><section-header><text><text><text><text><list-item><list-item><list-item><list-item></list-item></list-item></list-item></list-item></text></text></text></text></section-header></section-header></section-header></section-header>	1.2 A.M.		Dute.	2012.11.25
 ng/kg = ppm; 0.1wtll = 1000ppm n.d. = Not Detected (未檢出) MDL = Method Detection Limit (方法偵測極限值) * = Not Regulated (無規格值) * = Not Regulated (無規格值) **- = Qualitative analysis (No Unit) 定性分析(無單位) ***: 該物質是由"三丁基弱"、"三苯基錫"或各別元素(例如: 錦、鏡、砂、鉾或碑)之測試 結果計算得知。其NDL是針對"三丁基弱"、"三苯基锡"或元素(例如: 錦、鏡、砂、鉾或碑) 之評估. (The substance was calculated by the test results of Tributyl Tin, Triphenyl Tin or element (Ex. Antimony Beryllium Silicon Zinc or Phosphorus respectively). The MDL is evaluated for Tributyl Tin, Triphenyl Tin or element (Ex. Antimony Beryllium Silicon Zinc or Phosphorus respectively.)) 紅磯測試由SGS其他實驗室執行 (The Red phosphorus test was subcontracted to other SGS Laboratory.) 北島2012/3/7所發行KA/2012/30142之加發報告,原始資料請參考KA/2012/30142. (This is the additional test report of KA/2012/30142 which was issued on 2012/3/7. Please refer to KA/2012/30142 for original information.) 	 ng/kg = ppm; 0.1wtH = 1000ppm n.d. = Not Detected (未檢出) MDL = Method Detection Limit (方法偵測極限值) "-" = Not Regulated (急規移位) "-" = Not Regulated (急規移位) "** : 該物質是由"三丁基結", "三苯基錫"或各別元素(例如: 錦、鏡、砂、錦或頌)之測試 結果計算得知.其NDL是針對"三丁基錫", "三苯基錫"或名素(例如: 錦、鏡、砂、錦或頌)之測試 結果計算得知.其NDL是針對"三丁基錫", "三苯基锡"或元素(例如: 錦、鏡、砂、錦或頌)之測試 法果計算得知.其NDL是針對"三丁基錫", "三苯基锡"或元素(例如: 錦、鏡、砂、錦衣頌) 之評信. (The substance was calculated by the test results of Tributyl Tin, Triphenyl Tin or element (Ex. Antimony, Beryllium, Silicon、Zinc or Phosphorum respectively). The MDL is evaluated for Tributyl Tin, Triphenyl Tin or element (Ex. Antimony、Beryllium、Silicon、 Zinc or Phosphorus respectively.)) # 結構測試由SGS其他實驗室執行 (The Red phosphorus test mas subcontracted to other SGS Laboratory.) 此為2012/3/7所發行KA/2012/30142之加發報告,原始資料請參考KA/2012/30142. (This is the additional test report of KA/2012/30142 which was issued on 2012/3/7. Please refer to KA/2012/30142 for original information.) PPOS毫考實載(Reference Information): 持久技有機汚法物 POPs - (EU) 757/2010 PPOS毫大賞載(Cutlawing PPOS as substances or preparations in concentrations above 0.001% (10ppm), in semi-finished products or articles or parts at a level above 0.1%(1000ppm). in textiles or other coated 	 1. mg/k = pup : 0.1w1% = 100ppm 2. m.d. = Not Detected (未位式) 3. ML = Method Detection Limit (方法信約構得) 4 = Not Regulated (急波接道) 5 = Not Regulated (急波接道) 6 = Not Regulated (急波接道) 7	測詞 Tes 欣統酸例 SYNTON-1 新北市約 16F-3,1 TAIPE1	(本) (本) (本) (本) (本) (本) (本) (本)	.w	6 of 13
	PFOS濃度在物質或製備中不得超過0.001%(10ppm), 在半成品、成品或零部件中不得超過0.1%(1000ppm), 在紡績品或塗層材料 中不得超過1µg/m ² 。(Outlawing PFOS as substances or preparations in concentrations above 0.001% (10ppm), in semi-finished products or articles or parts at a level above 0.1%(1000ppm), in textiles or other coated	PPOS滾皮在物質或製備中不得超過0.001%(10ppm); 在半成品、成品或零邮件中不得超過0.1%(1000ppm); 在紡績品或塗層材料 中不得超過1µg/m ² * (Outlawing PPOS as substances or preparations in concentrations above 0.001% (10ppm), in semi-finished products or articles or parts at a level above 0.1%(1000ppm). In textiles or other coated materials above 1µg/m ² .)	7 8. PFOS 4- 4	 mg/kg = ppm; 0.1wtll = 1000ppm n.d. = Not Detected (未檢出) MDL = Method Detection Limit (方法偵測插限值) "-" = Not Regulated (急災格值) "-" = Not Regulated (急災格值) ***: 該物質是由"三丁基錫"、"三苯基錫"或各別元素(例知: 錦、皴、砂、鲜或竭結果計算得知, 其MDL是針對"三丁基錫"、"三苯基錫"或元素(例知: 錦、皴、趁、蜂花、(me substance was calculated by the test results of Tribut element (Ex. Antimony Beryllium Silicon Zinc or Phosphorus respectively.)) 紅璃測試由SGS其他實驗室執行 (The Red phosphorus test was subcontracted to 	、砂、鮮成場) syl Tin, Tripher setively). The 1 . Beryllium、Si o other SGS Lab This is the lease refer to	MDL is licon * oratory.)

